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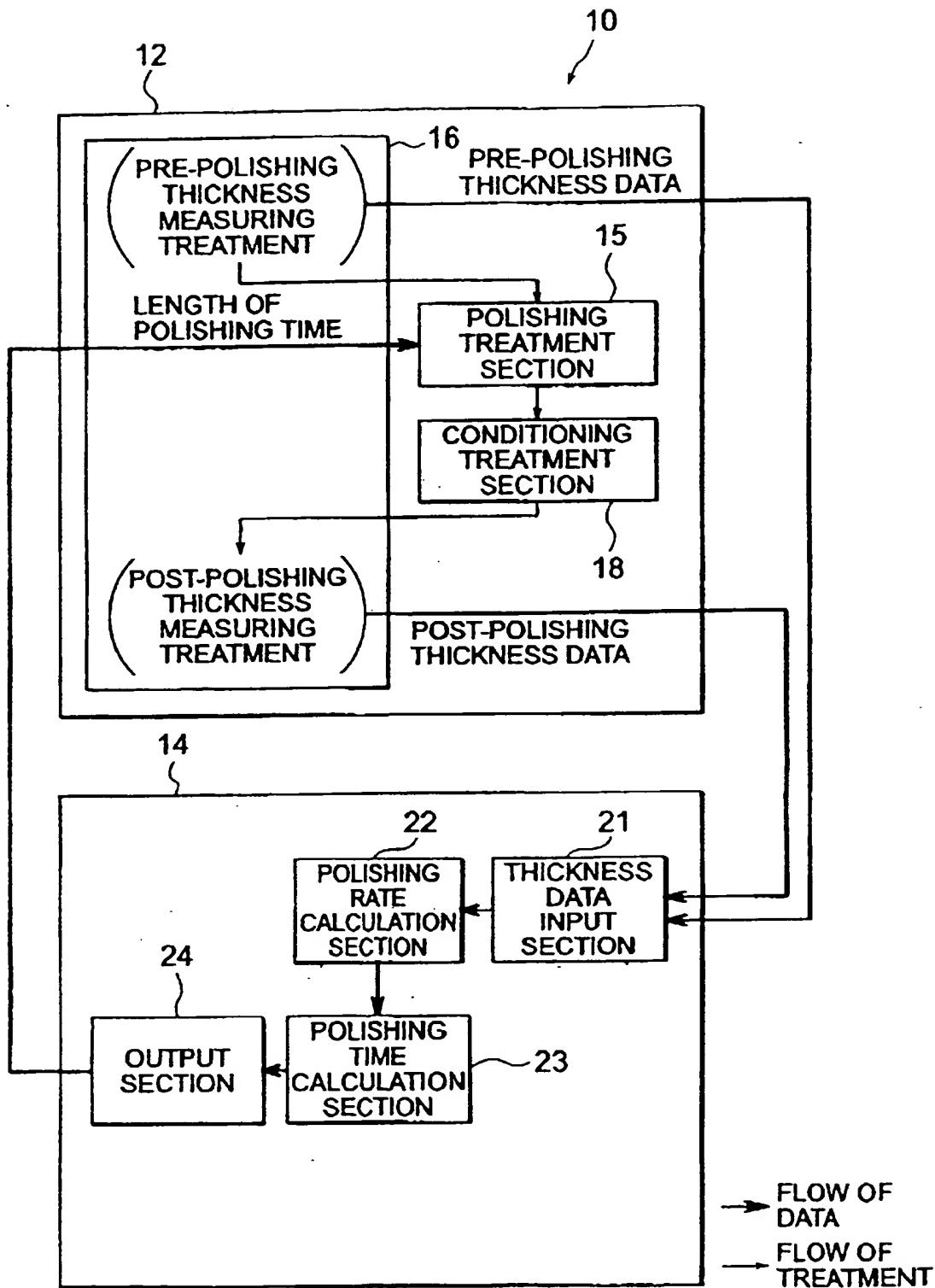
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(54) Abstract Title
Control of pad dresser in chemical-mechanical polishing apparatus

(57) A chemical-mechanical polishing apparatus comprises a polishing pad, a rotatable polishing table, a wafer holder, a pad dresser, means for calculating the wafer polishing rate and a controller for controlling the dresser based upon the polishing rate. The pad is dressed each time after a specified predetermined number of wafers have been polished, this number preferably being one or two. The polishing rate can be calculated based on film thickness before and after polishing in combination with the polishing time or it can be calculated based on the current or power required to rotate the polishing table and the wafer holder in combination with the polishing time. Dressing time or dressing force can be controlled on this basis.

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FIG. 1



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FIG. 2

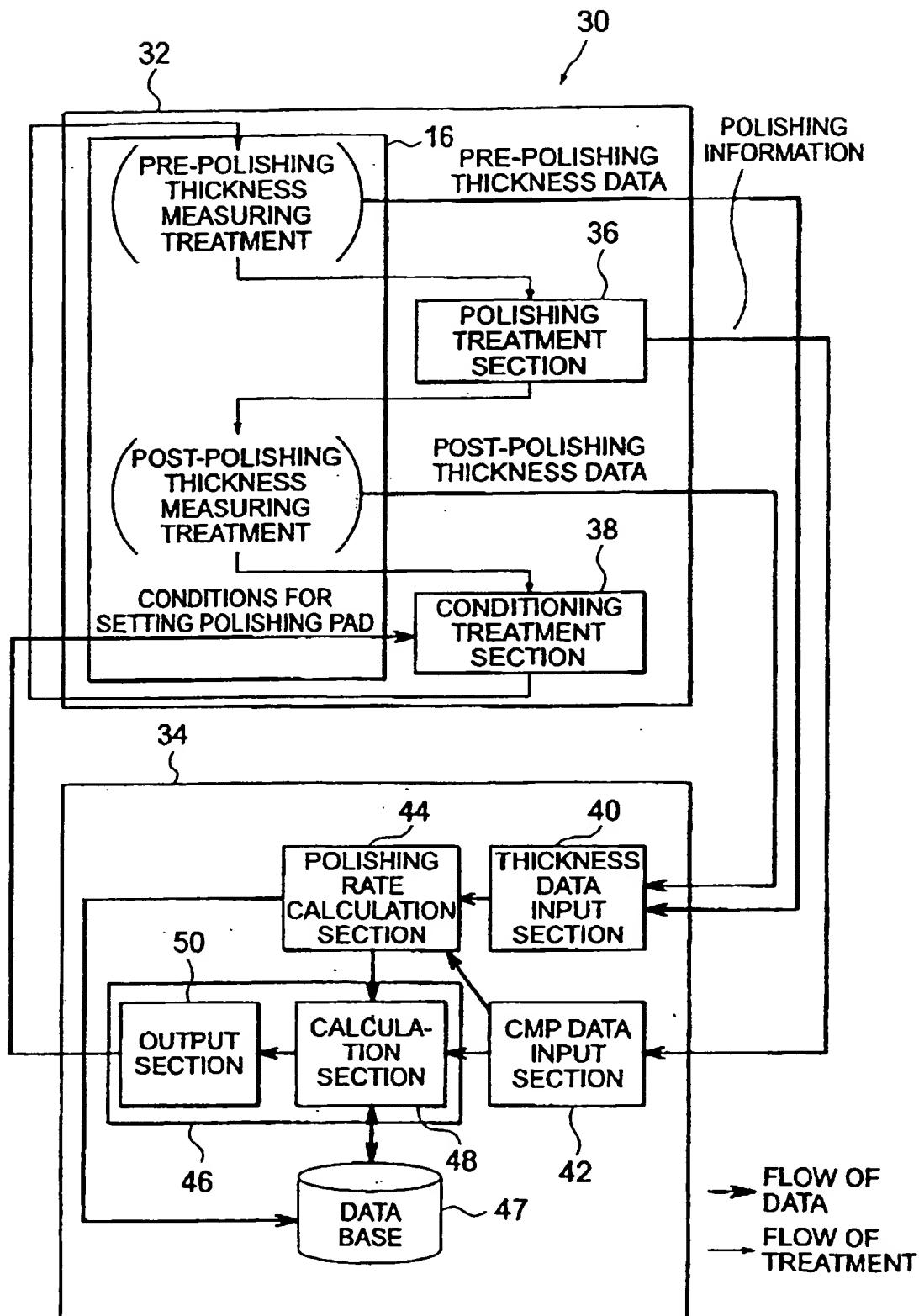


FIG. 3

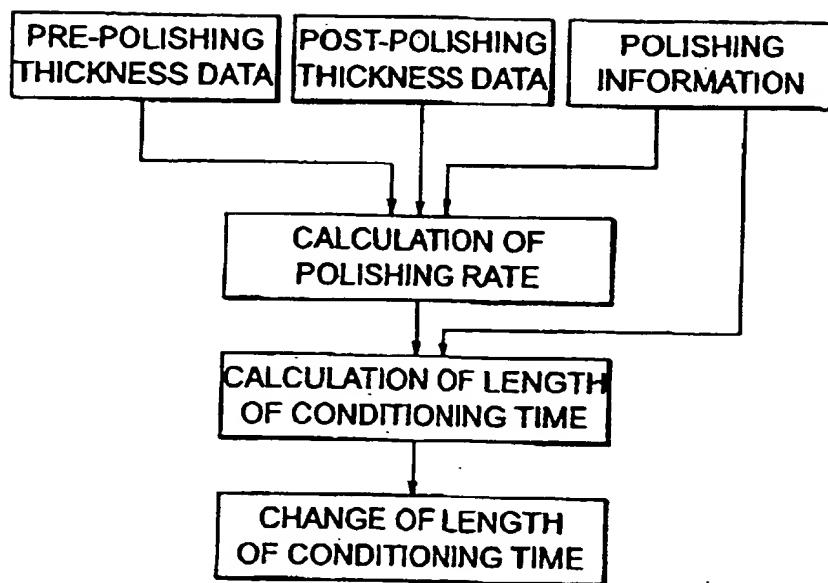


FIG. 4

KIND OF FILM: OXIDE FILM 1, PRODUCT NAME: 12345

CURRENT POLISHING RATE	1600	80	75	70	65	60
1500	85	80	75	70	65	
1400	90	85	80	75	70	
1300	95	90	85	80	75	
1200	100	95	90	85	80	
1100	105	100	95	90	85	
1000	110	105	100	95	90	
	-100	-50	0	50	100	

POLISHING RATE VARIATION AMOUNT

CONVERSION TABLES
ARE SELECTED FROM
DATA BASE BASED
ON KIND OF FILM AND
PRODUCT NAME

LENGTH OF
CONDITIONING
TIME IS CALCULATED
BASED ON CURRENT
POLISHING RATE AND
POLISHING RATE
VARIATION AMOUNT

EXAMPLE:

WHEN
 CURRENT POLISHING RATE $X=1250$
 POLISHING RATE VARIATION RATE $R=45$,
 CALCULATION IS CONDUCTED BY EMPLOYING
 THE BELOW PART OF THE CONVERSION TABLE
 BECAUSE
 $1200 \leq X \leq 1300$ AND $0 \leq R \leq 50$.

X1=1300	T1=85	T3=80
X2=1200	T2=90	T4=85
	RA=0	RB=50

LENGTH OF CONDITIONING TIME IS CALCULATED
BASED ON:
 $TA = ((T2-T1) / (X2-X1)) \times (X-X1) + T1$
 $TB = ((T4-T3) / (X2-X1)) \times (X-X1) + T3$
 $T = ((TB-TA) / (RB-RA)) \times (R-RA) + TA$
 AND IS ESMITATED $T=83$

FIG. 5

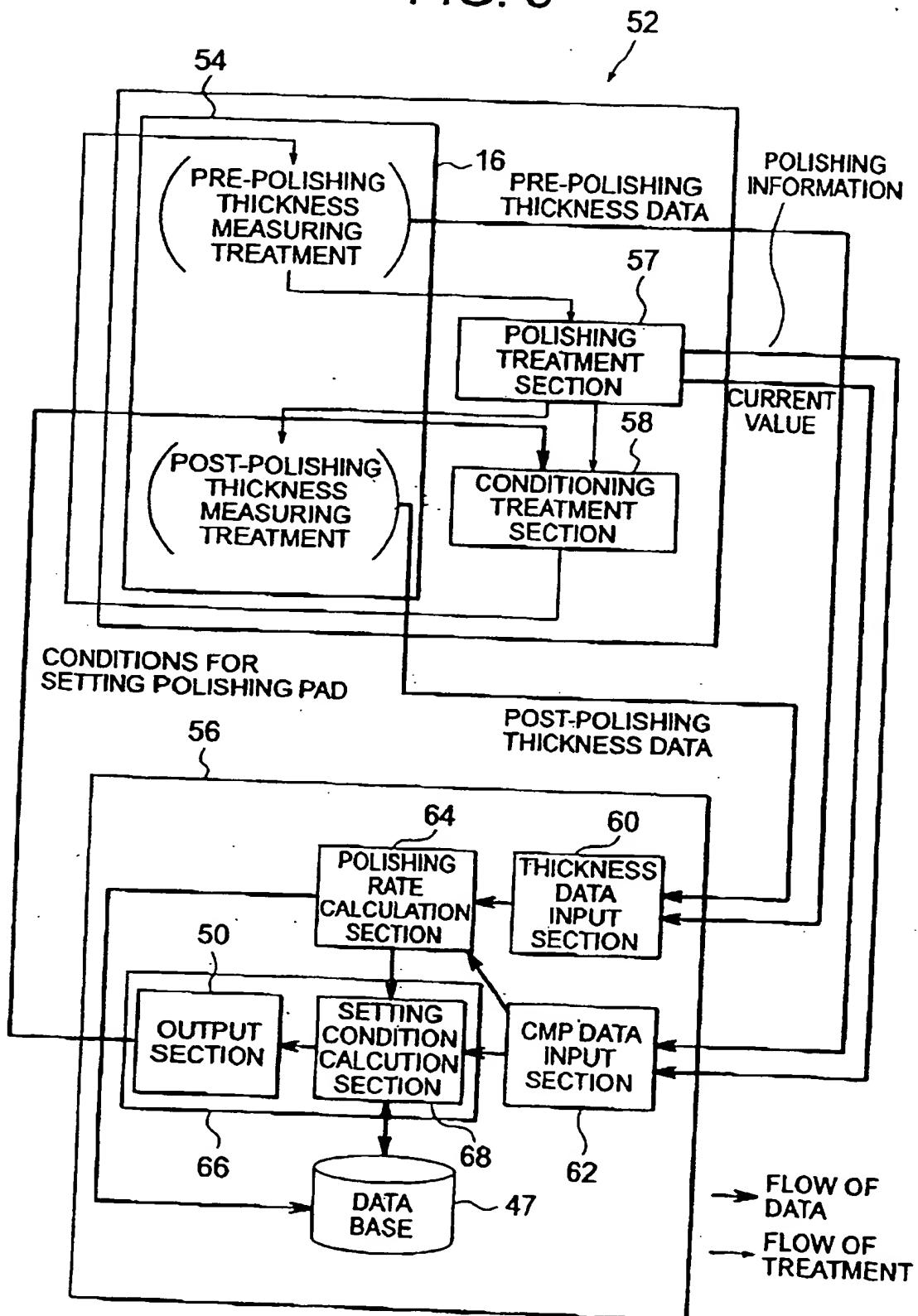


FIG. 6

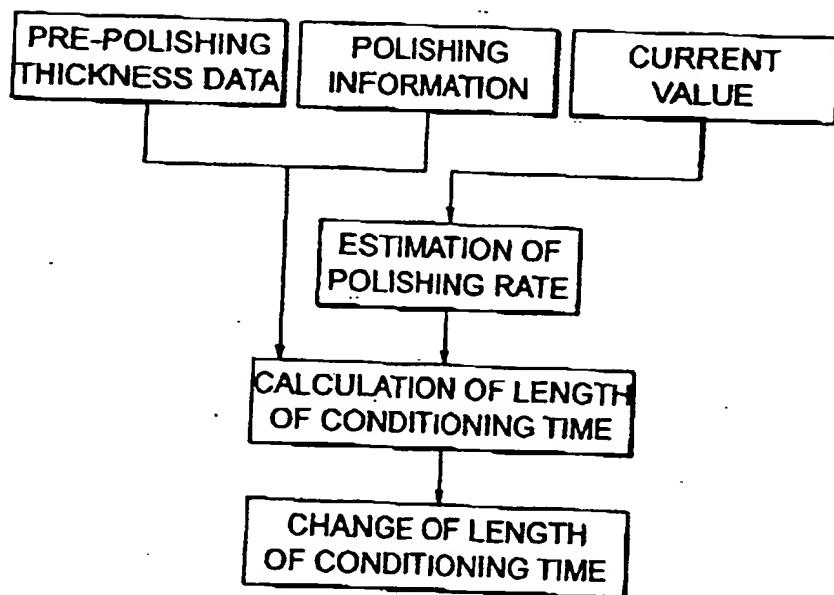
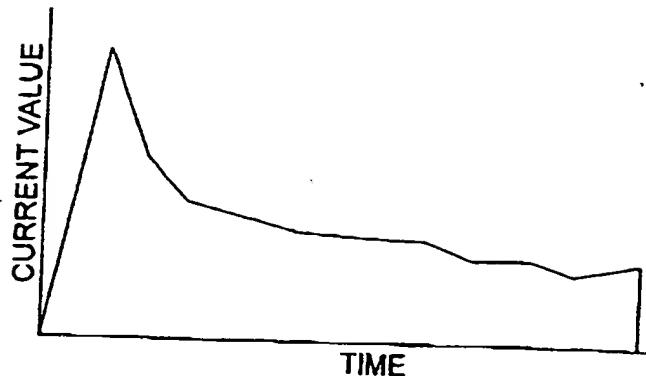


FIG. 7

CHARACTERISTICS SUCH AS VARIATION AMOUNT AND INTEGRATION AMOUNT ARE EXTRACTED FROM CURRENT VALUES SUPPLIED TO TABLE MOTOR AND SPINDLE MOTOR



KIND OF FILM: OXIDE FILM 1, PRODUCT NAME: 12345

CONVERSION TABLES ARE SELECTED FROM DATA BASE BASED ON KIND OF FILM AND PRODUCT NAME

CURRENT INTEGRATION VALUE

1600	80	75	70	65	60
1500	85	80	75	70	65
1400	90	85	80	75	70
1300	95	90	85	80	75
1200	100	95	90	85	80
1100	105	100	95	90	85
1000	110	105	100	95	90
	-100	-50	0	50	100

POLISHING RATE VARIATION AMOUNT

LENGTH OF CONDITIONING TIME IS CALCULATED BASED ON CURRENT POLISHING RATE AND POLISHING RATE VARIATION AMOUNT

EXAMPLE:

WHEN

CURRENT POLISHING RATE $X=1250$
POLISHING RATE VARIATION RATE $R=45$,
CALCULATION IS CONDUCTED BY EMPLOYING
THE BELOW PART OF THE CONVERSION TABLE
BECAUSE
 $1200 \leq X \leq 1300$ AND $0 \leq R \leq 50$.

X1=1300	T1=85	T3=80
X2=1200	T2=90	T4=85
	RA=0	RB=50

LENGTH OF CONDITIONING TIME IS CALCULATED BASED ON:
 $TA = ((T2-T1) / (X2-X1)) \times (X-X1) + T1$
 $TB = ((T4-T3) / (X2-X1)) \times (X-X1) + T3$
 $T = ((TB-TA) / (RB-RA)) \times (R-RA) + TA$
AND IS ESIMITATED $T=83$

CHEMICAL-MECHANICAL POLISHING**APPARATUS AND METHOD**

The present invention relates to a chemical-mechanical polishing apparatus and method. A particular chemical-mechanical polishing apparatus to be described below by way of example in illustration of the present invention is able to polish a wafer by a given amount.

5 In the manufacture of a semiconductor device, it has previously been proposed to employ a chemical-mechanical polishing apparatus (hereinafter referred to as a "CMP apparatus"). It is important to keep the amount of polishing within a fixed range when the polishing is carried out using the CMP apparatus. The CMP apparatus previously proposed has a controller
10 for controlling the length of polishing time.

An example of a previously proposed CMP apparatus will now be described by reference to Fig. 1 of the accompanying drawings, which shows by means of a block schematic diagram both an apparatus and a process.

15 The previously proposed CMP apparatus indicated at 10 in Fig. 1 has a polishing block 12 for polishing a film formed on a wafer, and a controller
14 for controlling the length of the polishing time.

The polishing block 12 includes a polishing treatment section 15 for polishing the film on the wafer, a thickness meter 16 for measuring the
20 thicknesses of the film before and after a polishing operation, and a conditioning treatment section 18 having a dresser for setting a polishing

pad. The polishing pad (not shown), a polishing table (not shown) which rotates while holding the polishing pad, a wafer holder (not shown), which rotates the film while pressing the film on a wafer or wafers on to the polishing pad, and a time section (not shown) for measuring the length of 5 the polishing time are included in the polishing treatment section 15.

The controller 14 includes a thickness data input section 21 for receiving film thickness data which is transmitted from the polishing block 12, a rate calculation section 22 for calculating both the polishing rate from the film thicknesses before and after the polishing operation, and the length 10 of the polishing time, a time calculation section 23 for calculating the length of the polishing time for the next wafer, and an output section 24 for transmitting the calculated length of the polishing time to the polishing block 12.

In order to polish the film on the wafer by employing the previously 15 proposed CMP apparatus 10, the film thickness before the polishing is first measured by the thickness meter 16 for measuring the film thicknesses, and the data obtained by this measurement (hereinafter referred to as "pre-polishing thickness data") is sent to the controller 14.

Then, a polishing treatment is carried out. Upon the completion of the 20 polishing operation, the CMP apparatus 10 carries out a setting treatment.

The film thickness after polishing is then measured by means of the thickness meter 16, and the data obtained by this measurement (hereinafter referred to as "post-polishing thickness data") is sent to the controller 14.

The controller 14 calculates both the current amount of polishing, based on

both the pre-polishing thickness data and the post-polishing thickness data, and the length of time required for the polishing treatment of the next wafer.

The length of time thus determined is sent to the polishing block 12.

- However, in the previously proposed CMP apparatus just described,
- 5 the length of the polishing time always varies, because, for example, the conditions for setting the polishing pad are not constant. The required length of the polishing time for a single wafer increases with every wafer that is polished. The length of the polishing time is at its least immediately after the setting of the polishing pad. Thus, disadvantages have been observed,
- 10 in that the amount of polishing of the wafer cannot be satisfactorily controlled, and in that the polishing pad is liable to be damaged and has a reduced life.

Features of a CMP apparatus to be described, by way of example in illustration of the present invention, are that the amount of polishing is more satisfactorily controlled, and that the polishing treatment is more stable than in the previously proposed arrangement.

A CMP apparatus to be described below by way of example in illustration of the present invention includes a polishing pad, a polishing table rotatable while holding the polishing pad, a wafer holder for pressing together a film on a wafer and the polishing pad, while the wafer is held, a dresser for setting the polishing pad each time after a specified number of the wafers have been chemically and mechanically polished, and a conditioning controller including a rate calculation section for calculating a polishing rate and an establishing section for establishing the conditions for

setting the polishing pad based on the calculated polishing rate.

In a particular CMP apparatus to be described below, by way of example in illustration of the present invention, after a predetermined number of the wafers has been polished, the setting conditions of the 5 polishing pad can be suitably corrected or the conditions of the polishing pad can be maintained nearly constant, and the polishing can be properly conducted. Accordingly, the CMP apparatus to be described can provide a more stabilized polishing rate and a satisfactory control of the amount of polishing. Further, any damage that may be caused to the polishing pad is 10 minimised. In arrangements to be described below by way of example in illustration of the present invention, it is preferable that the specified predetermined number of wafers is 1 or 2.

Arrangements which are illustrative of the present invention will now be described, by way of example with reference to Figs. 2 to 7 of the 15 accompanying drawings, in which:

Fig. 2 is a block schematic diagram for use in describing a first CMP apparatus and a treatment process carried out therein,

Fig. 3 is a block schematic diagram for use in describing in more detail the treatment process of the first CMP apparatus shown in Fig. 2,

20 Fig. 4 is a table for use in describing aspects of the treatment process of the first arrangement shown in Fig. 2,

Fig. 5 is a block schematic diagram for use in describing a second CMP apparatus and a treatment process carried out therein,

Fig. 6 is a block schematic diagram for use in describing the

treatment process of the second arrangement shown in Fig. 5, and

Fig. 7 is a table for use in describing aspects of the treatment process of the second arrangement shown in Fig. 5.

In describing the CMP apparatus and the steps in the treatment

- 5 carried out by the CMP apparatus of Fig. 2, similar elements to those described in relation to the arrangement of Fig. 1 will be indicated by the same reference numerals and no further detailed description of them will be given.

A CMP apparatus 30 shown in Fig. 2 has a polishing block 32 and a
10 conditioning controller 34 for establishing the setting conditions of a polishing pad. The conditioning controller 34 is connected to the polishing block 32 by means of a signal line for supplying and receiving signals.

The polishing block 32 includes a treatment section 36 for polishing a film on a wafer, a thickness meter 16 for measuring the film thicknesses
15 before and after the polishing operation and a conditioning treatment section 38 having a dresser for setting a polishing pad (not shown). The polishing pad, a polishing table (not shown), a wafer holder (not shown), and a timer section (not shown) for measuring the length of the polishing time are included in the treatment section 36.

20 The conditioning controller 34 includes a thickness data input section 40 for receiving film thickness data from the thickness meter 16 and a CMP data input section 42 for receiving polishing information, such as the length of the polishing time, as a polishing instruction from the polishing block 32.

The conditioning controller 34 further includes a calculation section 44

for calculating a polishing rate based on the data received from both of the input sections 40 and 42, an establishing section 46 for establishing the conditions for setting the polishing pad based on the calculated polishing rate, and a data base 47 for storing data. The establishing section 46

5 includes a calculation section 48 for calculating the required length of the setting time based on the polishing rate and the polishing information, and an output section 50 for transmitting the calculated length of the setting time to the conditioning treatment section 38. The data base 47 includes conversion tables for the calculation of the required setting time for each of

10 the combinations of the kinds of films and products, and the calculation section 48 carries out the transfer of the data to the data base 47.

A process of polishing carried out by the CMP apparatus 30 will now be described.

The pre-polishing thickness data relating to the film on the wafer

15 which is to be subjected to the CMP treatment is measured by the thickness meter 16, and transmitted to the thickness data input section 40.

Then, the wafer is sent to the polishing block 32 where it receives the polishing treatment. During the treatment, the polishing information (the length of polishing time and the degree of pressure on a spindle) and the

20 product information (the kind of films and the product name of the semiconductor device) are transmitted to the CMP data input section 42.

The wafer, upon the completion of the polishing treatment, is sent to the thickness meter 16 where the film thickness after the polishing operation is measured. The post-polishing thickness data is transmitted to the

thickness data input section 40.

- Thereafter, the calculation section 44 calculates the current polishing rate based on the pre-polishing thickness data and the post-polishing thickness data received by the thickness data input section 40 and the
5 length of the polishing time received by the CMP data input section 42.

The calculation section 48 calculates both the polishing rate variation value, which is the difference between the current polishing rate and the previous polishing rate, and the required length of setting time based on the current polishing rate, the polishing rate variation value and the conditioning
10 time conversion data tables of the data base 47 (refer to Fig. 3).

The calculation of the required length of the setting time can be carried out as follows.

The calculation section 48 extracts the required information from the data base 47 including the data stored in the conversion data tables in
15 relation to the product information, that is, in relation to the kind of the film in connection with the wafer being treated and the product name of the semiconductor. The required length of the setting time is calculated by means of an interpolation based on the required portions of the information extracted from the conversion data tables, the current polishing rate and the
20 polishing rate variation value.

The output section 50 transmits the calculated length of the setting time to the polishing block 32 which carries out a setting treatment based on the received length of the setting time.

The calculated data and the data received from the polishing block 32

are stored in the data base 47.

In the present arrangement being described, the setting conditions of the polishing pad can be maintained nearly constant, and the amount of the polished film on the wafer is nearly constant and is much more stabilized
 5 compared with that of the previously proposed arrangement. Further, the damage caused to the polishing pad is much less than that caused in the previously proposed arrangement.

A similar result can be obtained by calculating in a similar way the pressure conditions on the conditioning head by the calculation section 48,
 10 and by modifying the setting conditions in accordance with the calculated pressure conditions.

In the first described arrangement of which the treatment can be seen from the table of Fig. 4, the calculation section 48 calculates a required length of setting time by employing the following equations.

$$15 \quad TA = \{(X - X_1)/(X_2 - X_1) \times (T_2 - T_1) + T_1\} \dots\dots\dots(1)$$

$$TB = \{(X - X_1)/(X_2 - X_1) \times (T_4 - T_3) + T_3\} \dots\dots\dots(2)$$

$$T = \{(R - RA)/(RB - RA) \times (TB - TA) + TA\} \dots\dots\dots(3)$$

In these equations, X is a current polishing rate, X₁ and X₂ are an upper limit and a lower limit of a range in which X can exist, respectively,
 20 among the polishing rates included in the setting time calculation table. R is a polishing rate variation value, RA and RB are an upper value and a lower limit of a range in which R can exist, respectively, among the polishing rate variation values included in the setting time calculation table. T₁, T₂, T₃ and T₄ are required lengths of setting times corresponding to X₁ and RA, X₂

and RA, X1 and RB, and X2 and RB, respectively.

In this first described arrangement, the calculated polishing rate X was 1250, and the polishing rate variation amount R was 45. Based on these values, X1=1300, X2=1200, T1=85, T2=90, T3=80, T4=85, RA=0 and

- 5 RB=50 were obtained to calculate a required length of setting time T=83.

A CMP apparatus 52 of the second arrangement shown in Fig. 5 is different from the CMP apparatus 30 of the first described arrangement in that after the polishing of the wafer, the film thickness measurement and the setting of the polishing pad are carried out simultaneously. In describing the
10 second arrangement of Fig. 5, similar elements to those of the first arrangement of Fig. 2 are denoted by the same reference numerals and they will not be described in detail.

The CMP apparatus 52 includes a polishing block 54 which polishes a film on a wafer, and a conditioning roller 56 for establishing the setting
15 conditions of a polishing pad. The conditioning controller 56 is connected to the polishing block 54 by means of a signal line for supplying and receiving signals.

The polishing block 54 includes, in a similar way to the polishing block 32 of the first described arrangement of Fig. 2, a polishing treatment section
20 57 for polishing the film on the wafer, the thickness meter 16 for measuring the film thicknesses before and after the polishing operation, and a conditioning treatment section 58 having a dresser for setting the polishing pad (not shown). The polishing treatment section 57 includes the polishing pad, a polishing table (not shown), a wafer holder (not shown), and a device

for measuring the length of the polishing time (not shown). The polishing block 54 further includes a motor table for rotating the polishing table, and a motor having a spindle for rotating the wafer holder (both of which are not shown).

- 5 The conditioning controller 56 includes, in a similar way to the conditioning controller 14, a thickness data input section 60 and a CMP data input section 62.

The conditioning controller 56 further includes a calculation section 64 which calculates the polishing rate from the values of the film thicknesses
10 before and after polishing and the length of the polishing time, and calculates the polishing rate, based on polishing information received from the polishing block 54 during the polishing, an establishment section 66 for establishing the setting conditions of the polishing pad based on the calculated polishing rate and a data base 47 for storing the data. The
15 calculation section 64 calculates the polishing rate based on the values of the current supplied to the motor having a table, and the motor having a spindle, and on the length of the polishing time. The establishment section 66 includes a setting conditions calculation section 68 for calculating a required length of the setting time based on the polishing rate and a
20 polishing instruction, and an output section 50 for transmitting the required length of the setting time to the conditioning treatment section 58. The data base 47 includes conditioning time conversion tables similar to those of the first example described with reference to Fig. 2, and the setting conditions calculation section 68 carries out the transfer of the data to the data base 47.

The process of polishing carried out by CMP apparatus 30 will now be described referring to Fig. 6.

The pre-polishing thickness data of the film on the wafer which is to be subjected to the CMP treatment are measured by means of the thickness meter 16, and transmitted to the film thickness data input section 60.

Then, the wafer is sent to the polishing block 54 and receives the polishing treatment. During the treatment, polishing information (the length of the polishing time and the degree of pressure on the spindle), the values of the current supplied to the motor having a table and the motor having a spindle, and product information (the kind of film and the product name of a semiconductor device) are transmitted to the CMP data input section 62.

Upon the completion of the polishing treatment, the wafer is sent to the thickness meter 16 and the film thickness after the polishing operation is measured. The post-polishing thickness data is transmitted to the film thickness data input section 60.

Simultaneously therewith, the polishing rate calculation section 64 calculates the current polishing rate based on the values of the current supplied to the motor having a table and the motor having a spindle and on the length of the polishing time, and estimates the conditions for the polishing pad.

The conditioning time conversion data tables associated with the particular kind of the film currently being treated and the product name of the semiconductor are extracted from the data base 47 and received.

Thereafter, a required length of setting time is calculated and

transmitted to a conditioning treatment section 58 in a similar way to the first described arrangement of Fig. 2.

Upon the completion of the measurement of the film thickness after the polishing operation, the polishing rate calculation section 64 calculates
5 the precise value of the current polishing rate based on the pre-polishing thickness data and the post-polishing thickness data received by the film thickness data input section 60 and the length of the polishing time received by the CMP data input section 62, and stores the precise data in the data base 47. The precise data is employed as data for improving the accuracy
10 of a subsequent setting treatment.

Similar improved effects to those of the example described with reference to Fig. 2 can be obtained by means of the arrangement of Fig. 5. The amount of polishing can be sufficiently controlled even if the CMP apparatus 52 does not have the thickness meter 16.

15 With regard to the second arrangement illustrated in Fig. 5, reference is made to a graph showing the relation between the length of polishing time and the values of the current of a motor having a table and a motor having a spindle, and a polishing rate is calculated based on the graph and in accordance with the procedure shown in Fig. 7. The calculated polishing rate X was 1250, and a variation amount R of the polishing rate was 45.
20 Based on these values, the results $X_1=1300$, $X_2=1200$, $T_1=85$, $T_2=90$, $T_3=80$, $T_4=85$, $RA=0$ and $RB=50$ were obtained, similar to those of the first arrangement described with reference to Fig. 2, to calculate a required length of setting time $T=83$.

Thereafter, the precise value of the polishing rate was calculated based on the pre-polishing thickness data and the post-polishing thickness data and was stored in the data base 47.

The above arrangements have been described only as examples, and

5 the scope of the protection sought is not limited to the above illustrative arrangements.

It will be understood that, although particular arrangements have been described, by way of example in illustration of the invention, variations and modifications thereof, as well as other arrangements, may be conceived

10 within the scope of the appended claims.

CLAIMS

1. A chemical-mechanical polishing (CMP) apparatus including a polishing pad, a polishing table rotatable while holding the polishing pad, a wafer holder so arranged that a film on a wafer and the polishing pad are pressed together while the wafer is held, and a dresser for setting the polishing pad each time after a specified predetermined number of the wafers has been chemically and mechanically polished, a conditioning controller including a rate calculation section for calculating a polishing rate and an establishing section for establishing conditions for setting the polishing pad based on the calculated polishing rate.
2. A CMP apparatus as claimed in claim 1, in which the rate calculation section calculates the polishing rate based on film thicknesses before and after the polishing of the film and on the length of the polishing time.
3. A CMP apparatus as claimed in claim 1, in which the polishing rate calculation section calculates the polishing rate based on the current power required for rotating the polishing table and the wafer holder during the polishing and the length of polishing time.
4. A CMP apparatus as claimed in claim 1, wherein the condition

establishing section establishes the required length of the setting time in accordance with the correlation between the polishing rate and the required length of the setting time.

5 5. A CMP apparatus as claimed in claim 4, in which the correlation is determined from a graph.

6. A CMP apparatus as claimed in claim 4, in which the correlation is determined from a table.

10 7. A CMP apparatus as claimed in claim 1, in which the condition establishing section establishes a required pressing force of a dresser upon the polishing pad in accordance with the correlation determined in advance between the polishing rate and the required length of the setting time.

15 8. A CMP apparatus as claimed in claim 7, in which the correlation is determined from a graph.

20 9. A CMP apparatus as claimed in claim 7, in which the correlation is determined from a table.

10. A CMP apparatus as claimed in claim 9, in which the condition establishing section establishes the conditions by the interpolation of the correlation determined from the table.

11. A method of operating a CMP apparatus as claimed in claim 1 substantially as described herein with reference to Figs. 2-4 or 5 to 7 of the accompanying drawings.

5

12. A CMP apparatus as claimed in claim 1 substantially as described herein with reference to Figs. 2-4, or 5 to 7, of the accompanying drawings.



Application No: GB 9924527.6
Claims searched: 1-12

Examiner: Matthew Lawson
Date of search: 13 July 2000

Patents Act 1977
Search Report under Section 17

Databases searched:

UK Patent Office collections, including GB, EP, WO & US patent specifications, in:

UK Cl (Ed.R): B3D (DDCC, DDCN, DDCX, DMN)

Int Cl (Ed.7): B24B 37/00, 37/04, 49/18, 51/00, 53/00

Other: Online: PAJ, WPI

Documents considered to be relevant:

Category	Identity of document and relevant passage	Relevant to claims
X	EP 0829327 A1 (SPEEDFAM) - the whole document.	1 at least
X,P	JP 110138418 A (MATSUSHITA) - published 25-05-99 - figures 1, 3 & 5 and WPI Abstract Accession No. 99-365676/31.	1 at least
X	JP 100015807 A (CANON) - figure 1 and the PAJ abstract.	1 at least
X	US 5664987 (RENTELN) - column 2 lines 28-49, column 3 line 21 - column 4 line 21, column 6 lines 43-51 and figure 2.	1,2,4-10

X	Document indicating lack of novelty or inventive step	A	Document indicating technological background and/or state of the art.
Y	Document indicating lack of inventive step if combined with one or more other documents of same category.	P	Document published on or after the declared priority date but before the filing date of this invention.
&	Member of the same patent family	E	Patent document published on or after, but with priority date earlier than, the filing date of this application.